# The RF Line **NPN Silicon RF Power Transistor**

- ... designed for power amplifier applications in industrial, commercial and amateur radio equipment to 30 MHz.
- Specified 12.5 Volt, 30 MHz Characteristics Output Power = 60 Watts Minimum Gain = 13 dB Efficiency = 55%

## **MATCHING PROCEDURE**

In the push-pull circuit configuration it is preferred that the transistors are used as matched pairs to obtain optimum performance.

The matching procedure used by Motorola consists of measuring hee at the data sheet conditions and color coding the device to predetermined hFE ranges within the normal h<sub>FF</sub> limits. A color dot is added to the marking on top of the cap. Any two devices with the same color dot can be paired together to form a matched set of units.

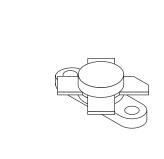
## **MAXIMUM RATINGS**

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Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V <sub>CEO</sub>	18	Vdc
Collector–Emitter Voltage	V <sub>CES</sub>	36	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector Current — Continuous	I <sub>C</sub>	15	Adc
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	175 1.0	Watts W/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C

## **MRF455**

60 W, 30 MHz **RF POWER TRANSISTOR NPN SILICON** 



**CASE 211-07, STYLE 1** 

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•		•	•
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	18	_	_	Vdc
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 50 mAdc, V <sub>BE</sub> = 0)	V <sub>(BR)</sub> CES	36	_	_	Vdc
Emitter–Base Breakdown Voltage $(I_E = 10 \text{ mAdc}, I_C = 0)$	V <sub>(BR)EBO</sub>	4.0	_	_	Vdc
ON CHARACTERISTICS		•		•	•
DC Current Gain (I <sub>C</sub> = 5.0 Adc, V <sub>CE</sub> = 5.0 Vdc)	h <sub>FE</sub>	10	_	150	_
DYNAMIC CHARACTERISTICS	-	•	•	•	•
Output Capacitance	C <sub>ob</sub>	_	_	250	pF

(continued)

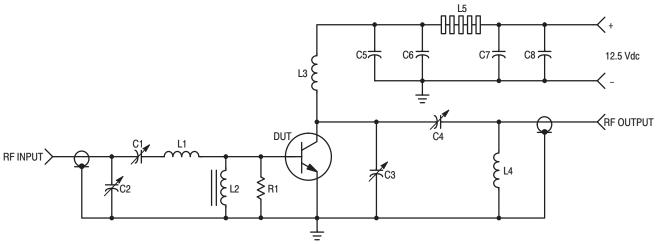


 $(V_{CB} = 12.5 \text{ Vdc}, I_{E} = 0, f = 1.0 \text{ MHz})$ 

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**ELECTRICAL CHARACTERISTICS** — **continued** (T<sub>C</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
FUNCTIONAL TESTS (Figure 1)	·				
Common–Emitter Amplifier Power Gain (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 60 W, f = 30 MHz)	G <sub>pe</sub>	13	_	_	dB
Collector Efficiency (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 60 W, f = 30 MHz)	η	55	_	_	%
Series Equivalent Input Impedance (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 60 W, f = 30 MHz)	Z <sub>in</sub>	_	1.66-j.844	_	Ohms
Series Equivalent Output Impedance (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 60 W, f = 30 MHz)	Z <sub>out</sub>	_	1.73-j.188	_	Ohms
Parallel Equivalent Input Impedance (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 60 W, f = 30 MHz)	Z <sub>in</sub>	_	2.09/1030	_	Ω/pF
Parallel Equivalent Output Impedance (V <sub>CC</sub> = 12.5 Vdc, P <sub>out</sub> = 60 W, f = 30 MHz)	Z <sub>out</sub>	_	1.75/330	_	Ω/pF



C1, C2, C4 — ARCO 469

C3 — ARCO 466

C5 — 1000 pF, UNELCO

C6, C7 —  $0.1 \,\mu\text{F}$  Disc Ceramic

C8 — 1000 µF/15 V Electrolytic

R1 — 10 Ohm/1.0 Watt, Carbon

L1 — 3 Turns, #18 AWG, 5/16" I.D., 5/16" Long

L2 — VK200-20/4B, FERROXCUBE

L3 — 12 Turns, #18 AWG Enameled Wire, 1/4" I.D., Close Wound

L4 — 3 Turns 1/8" O.D. Copper Tubing, 3/8" I.D., 3/4" Long

L5 — 7 FERRITE Beads, FERROXCUBE #56–590–65/3B

Figure 1. 30 MHz Test Circuit Schematic

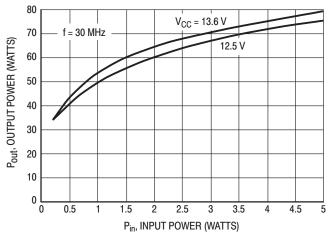


Figure 2. Output Power versus Input Power

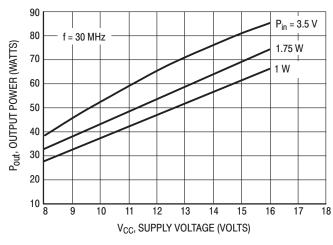
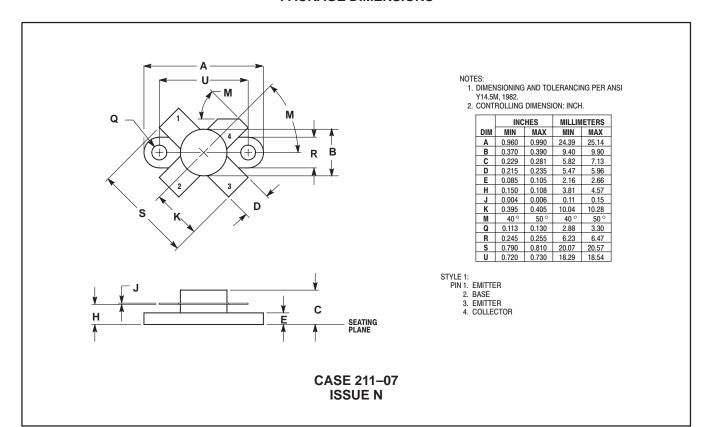


Figure 3. Output Power versus Supply Voltage

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